



U.S.S.N. 107606,823

Listing of Claims

Claims 1- 24(canceled)

25. (previously presented) The method of claim 39, further comprising exposing the defectively exposed portion to the second mask part a second time.

26. (previously presented) The method of claim 25, further comprising exposing the defectively exposed portion to the second mask part a third time.

27. (previously presented) The method of claim 39, further comprising exposing the defectively exposed portion to the second mask part one or more additional times.

28. (previously presented) The method of claim 39 further comprising exposing the defectively exposed portion to the second, a third and other additional mask parts one or more additional times.

29. (previously presented) The method of claim 39, wherein the first mask part comprises a layout for a semiconductor device that is at least partially defective, and the second mask part comprises the layout for the semiconductor device that is at

U.S.S.N. 10/606,823

least substantially free from defects or with defects at different locations.

30. (previously presented) The method of claim 39, wherein exposing the semiconductor wafer to the first mask part and exposing the defectively exposed portion to the second mask part comprise a lithographic semiconductor fabrication process.

31. (cancelled)

32. (previously presented) The method of claim 39, wherein the first mask part and the second mask part are on a same photomask.

33. (previously presented) The method of claim 39, wherein the first mask part and the second mask part are on different photomasks.

Claims 34-38 (cancelled)

39. (previously presented) A method for repairing a defectively exposed semiconductor wafer comprising:

 exposing a semiconductor wafer to a first mask part that is at least partially defective to form a defectively exposed

U.S.S.N. 10/606,823

portion; and,

exposing the defectively exposed portion to a second mask part corresponding to the first mask part and that is at least substantially free from defects or with defects at different locations to at least partially repair said defectively exposed portion.